

ST2001HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

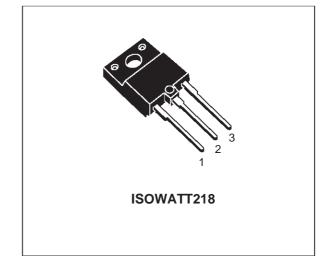
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

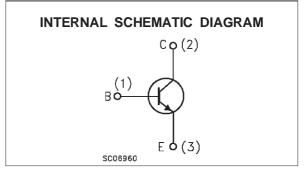
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TV AND MONITOR

DESCRIPTION

The ST2001HI is manufactured using collector diffused technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage $(I_E = 0)$	1500	V
Vceo	Collector-Emitter Voltage $(I_B = 0)$	600	V
V _{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
lc	Collector Current	10	A
ICM	Collector Peak Current (t _p < 5 ms)	20	Α
IB	Base Current	7	A
P _{tot}	Total Dissipation at $T_c = 25$ °C	55	W
T_{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	2.3	°C/W
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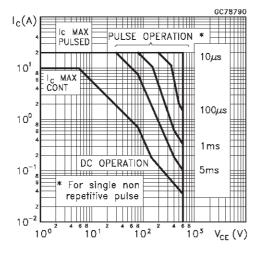
ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \,^{\circ}C$ unless otherwise specified)

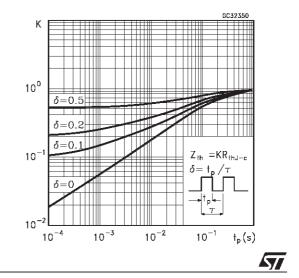
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V _{BE} = 0)	$V_{CE} = 1500 V$ $V_{CE} = 1500 V$ $T_j = 125 °C$			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	$V_{EB} = 7 V$			1	mA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	I _C = 100 mA L = 25 mH	600			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = 5 \ {\rm A}$ $I_{\rm B} = 1.25 \ {\rm A}$			1.5	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A I _B = 1.25 A			1.2	V
h _{FE} *	DC Current Gain	Ic = 6 A V _{CE} = 5 V	5		10	
	INDUCTIVE LOAD	I _C =5 A I _{BON(END)} =1 A				
ts	Storage Time	$L_B = 1 \ \mu H$ $V_{BB} = -2.5 \ V$		2.5	3.5	μs
t _f	Fall Time	f = 64 KHz		0.3	0.45	μs

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

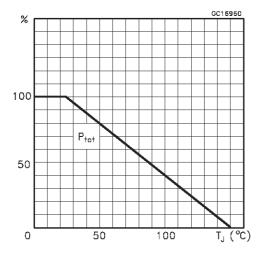
Safe Operating Area

Thermal Impedance

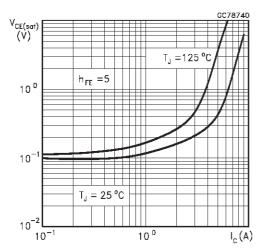




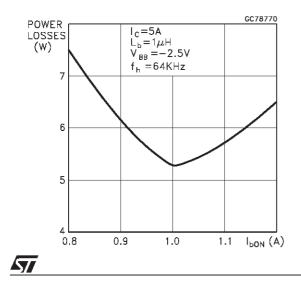
Derating Curve



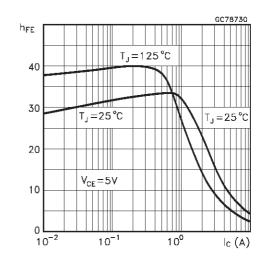
Collector Emitter Saturation Voltage



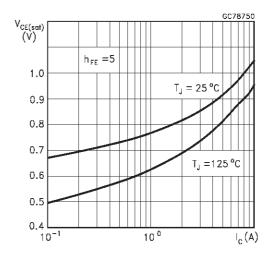
Power Losses

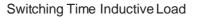


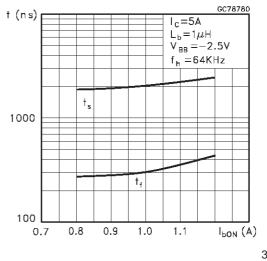
DC Current Gain



Base Emitter Saturation Voltage

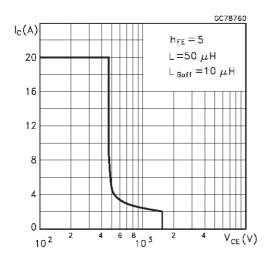




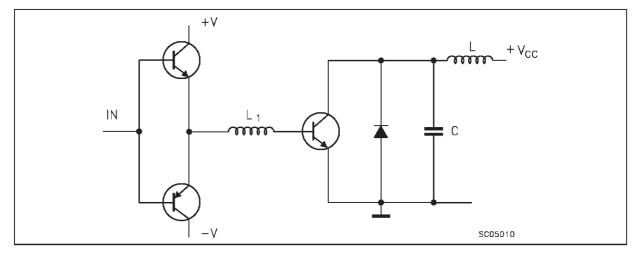


ST2001HI

RBSOA

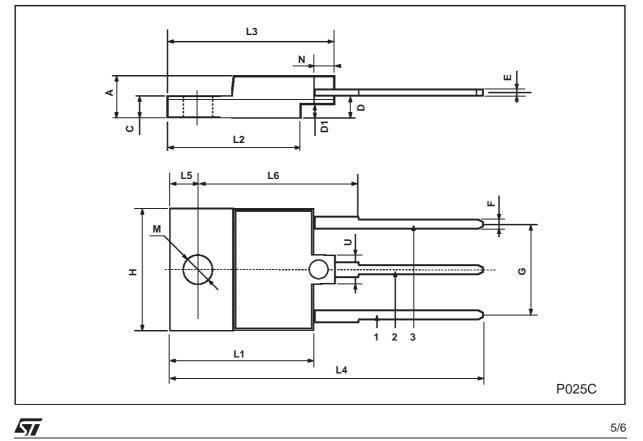


Inductive Load Switching Test Circuits.



DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.210		0.222
С	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
Н	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
М	3.5		3.7	0.137		0.145
Ν	2.1		2.3	0.082		0.090
U		4.6			0.181	





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